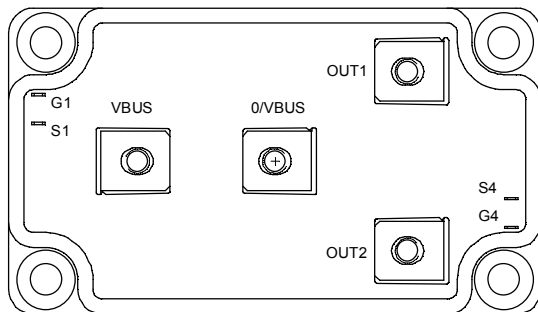
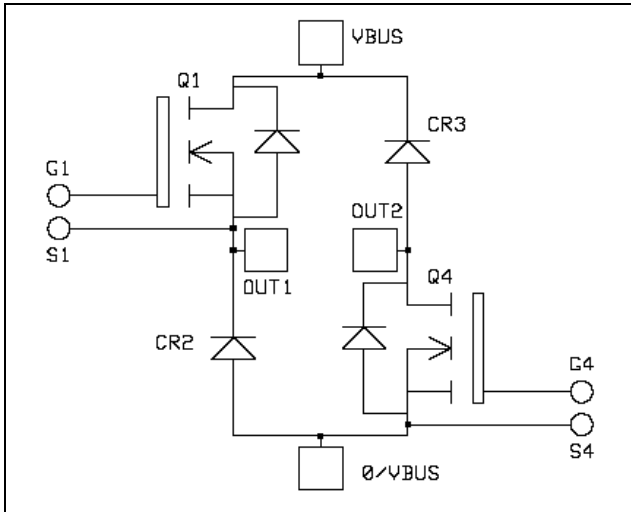


***Asymmetrical - bridge
MOSFET Power Module***

**$V_{DSS} = 200V$
 $R_{DSon} = 10m\Omega \text{ max @ } T_j = 25^\circ C$
 $I_D = 175A \text{ @ } T_c = 25^\circ C$**



Application

- Welding converters
- Switched Mode Power Supplies
- Switched Reluctance Motor Drives

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile

Absolute maximum ratings

<i>Symbol</i>	<i>Parameter</i>	<i>Max ratings</i>	<i>Unit</i>
V_{DSS}	Drain - Source Breakdown Voltage	200	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	175
		$T_c = 80^\circ C$	131
I_{DM}	Pulsed Drain current	700	A
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	10	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	694
I_{AR}	Avalanche current (repetitive and non repetitive)	89	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	2500	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{DSS}	Drain - Source Breakdown Voltage	$V_{GS} = 0V, I_D = 375\mu A$	200			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 200V, T_j = 25^\circ\text{C}$			150	μA
		$V_{GS} = 0V, V_{DS} = 160V, T_j = 125^\circ\text{C}$			750	
$R_{DS(on)}$	Drain - Source on Resistance	$V_{GS} = 10V, I_D = 87.5A$			10	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5mA$	3		5	V
I_{GSS}	Gate - Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		13.7		nF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		4.36		
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$		0.2		
Q_g	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 100V$ $I_D = 150A$		224		nC
Q_{gs}	Gate - Source Charge			86		
Q_{gd}	Gate - Drain Charge			94		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 133V$ $I_D = 150A$ $R_G = 2.5\Omega$		28		ns
T_r	Rise Time			56		
$T_{d(off)}$	Turn-off Delay Time			81		
T_f	Fall Time			99		
E_{on}	Turn-on Switching Energy ❶	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 133V$ $I_D = 150A, R_G = 2.5\Omega$		926		μJ
E_{off}	Turn-off Switching Energy ❷			910		
E_{on}	Turn-on Switching Energy ❶	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 133V$ $I_D = 150A, R_G = 2.5\Omega$		1216		μJ
E_{off}	Turn-off Switching Energy ❷			1062		

Diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle, $T_c = 90^\circ\text{C}$		200		A
V_F	Diode Forward Voltage	$I_F = 200A$		1		V
		$I_F = 400A$		1.4		
		$I_F = 200A, T_j = 125^\circ\text{C}$		0.9		
t_{rr}	Reverse Recovery Time	$I_F = 200A$ $V_R = 133V$ $di/dt = 400A/\mu s$	$T_j = 25^\circ\text{C}$	60		ns
			$T_j = 125^\circ\text{C}$	110		
Q_{rr}	Reverse Recovery Charge	$I_F = 200A$ $V_R = 133V$ $di/dt = 400A/\mu s$	$T_j = 25^\circ\text{C}$	400		nC
			$T_j = 125^\circ\text{C}$	1680		

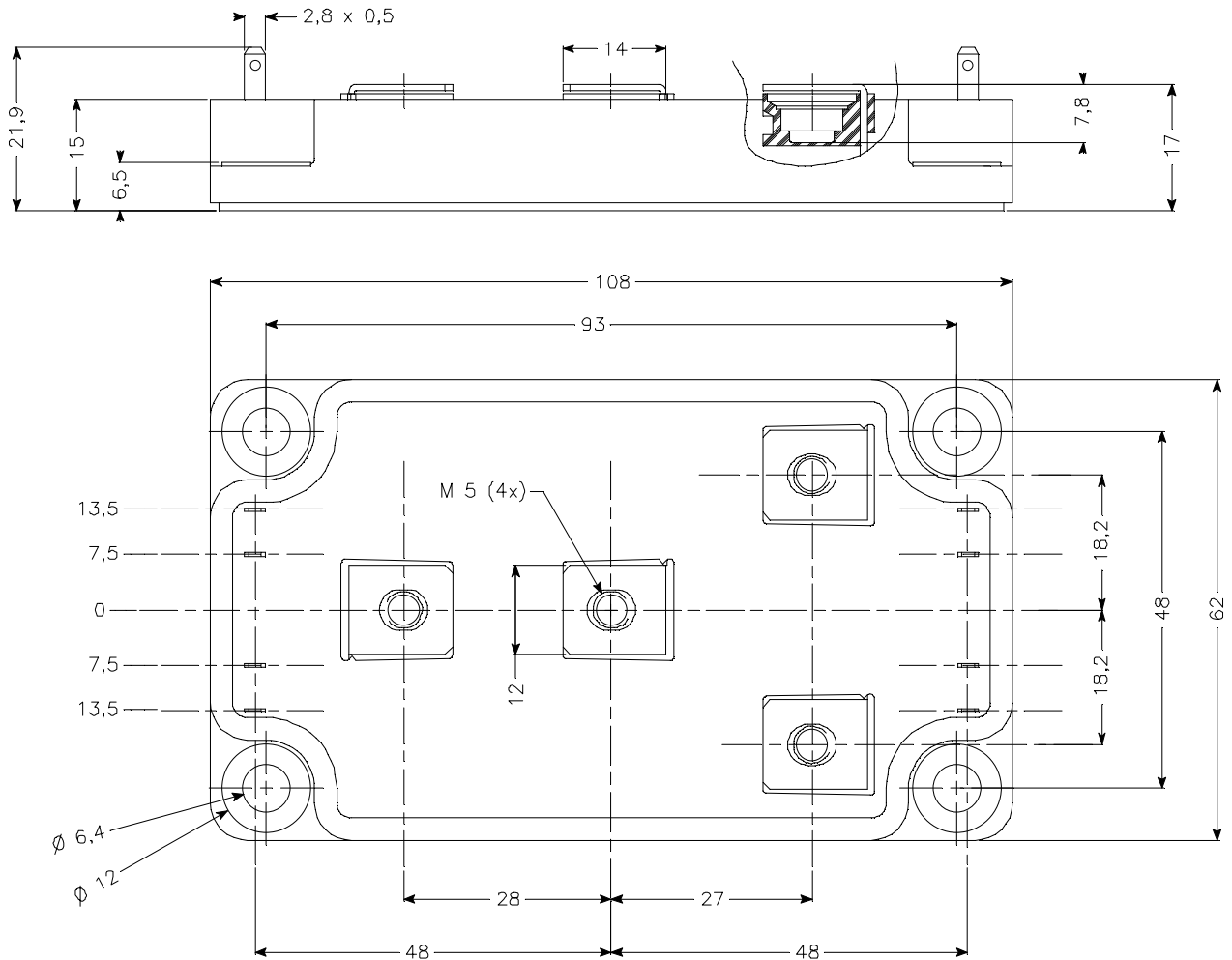
❶ E_{on} includes diode reverse recovery.

❷ In accordance with JEDEC standard JESD24-1.

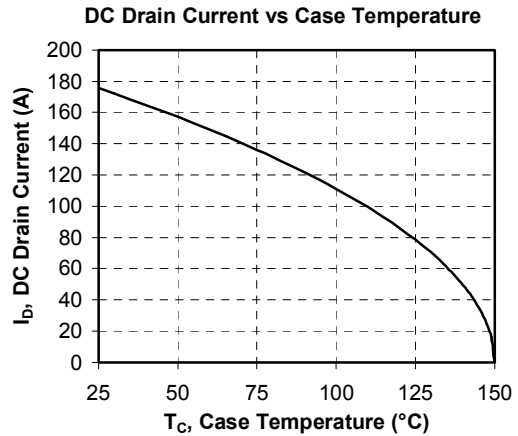
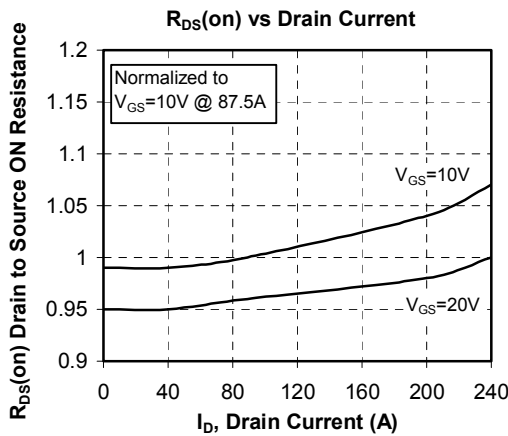
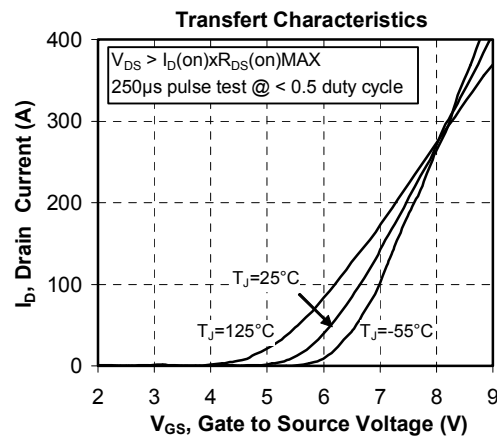
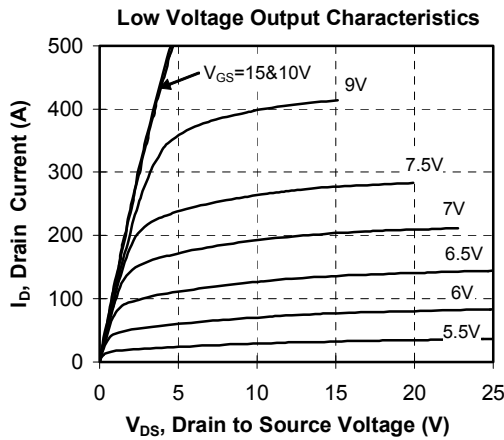
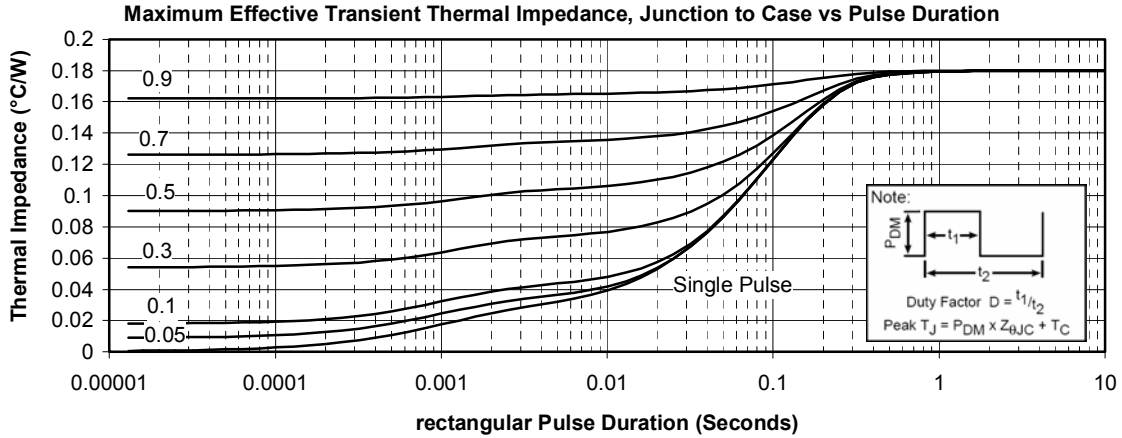
Thermal and package characteristics

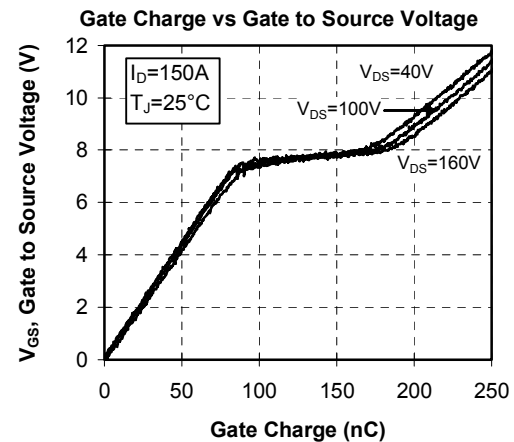
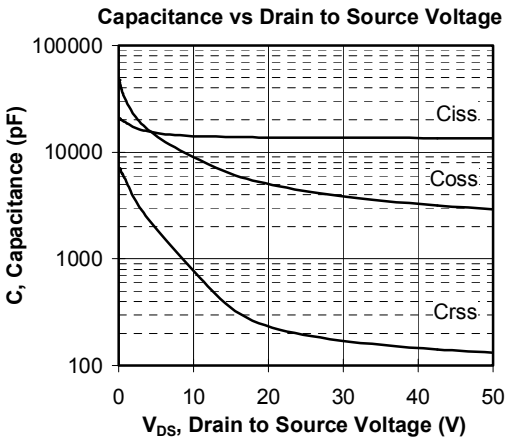
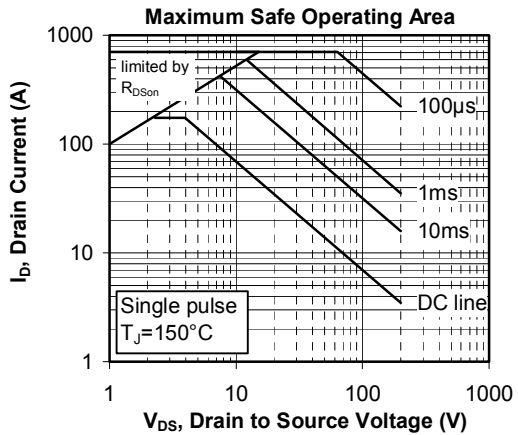
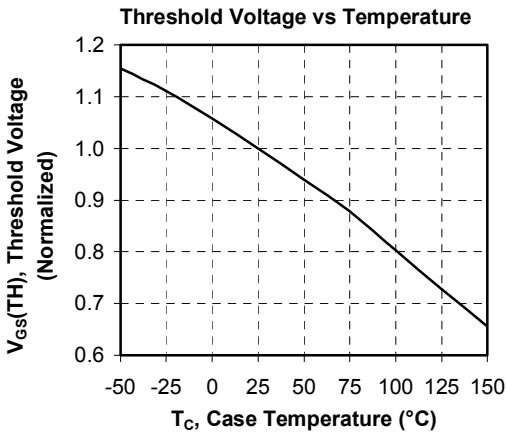
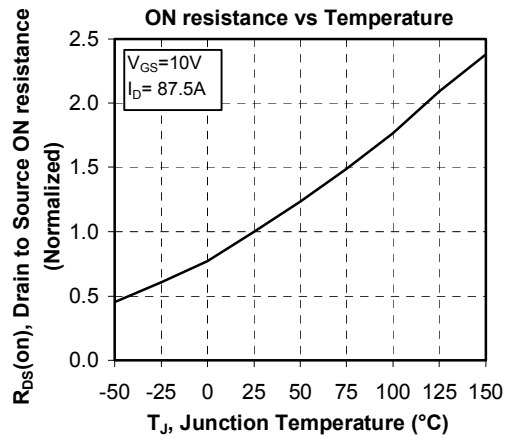
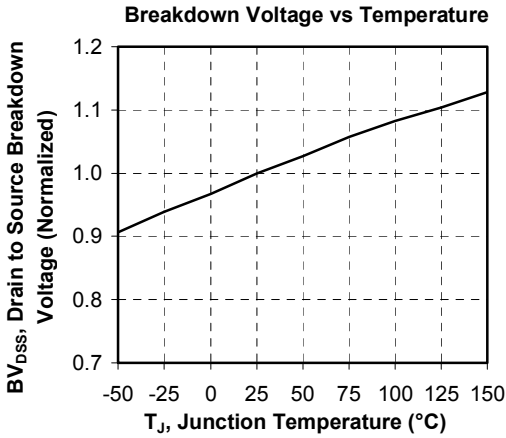
Symbol	Characteristic		Min	Typ	Max	Unit
R _{thJC}	Junction to Case	Transistor			0.18	°C/W
		Diode			0.32	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz		2500			V
T _J	Operating junction temperature range		-40		150	°C
T _{STG}	Storage Temperature Range		-40		125	
T _C	Operating Case Temperature		-40		100	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package Weight				280	g

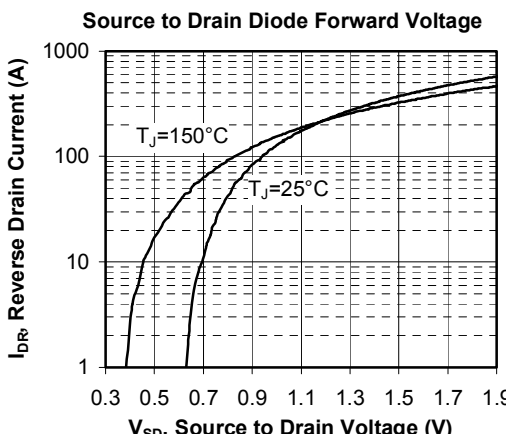
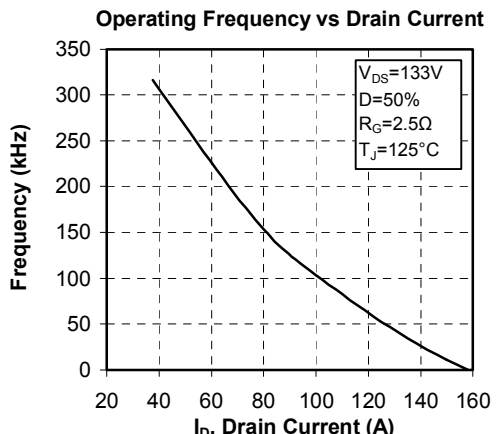
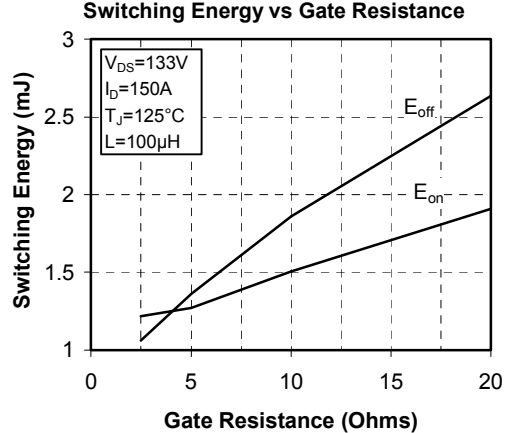
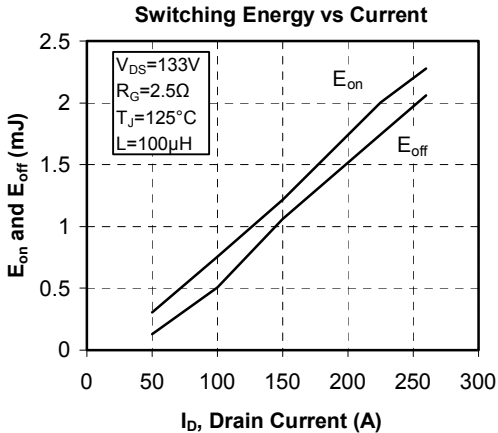
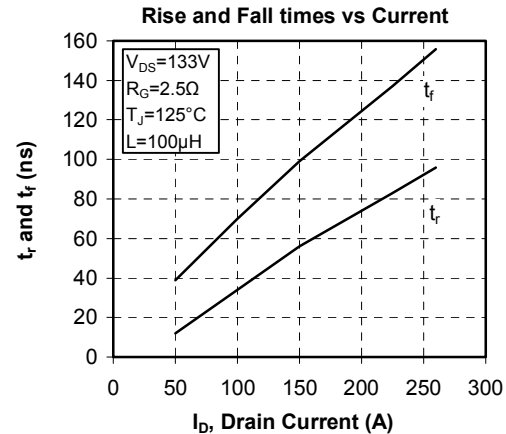
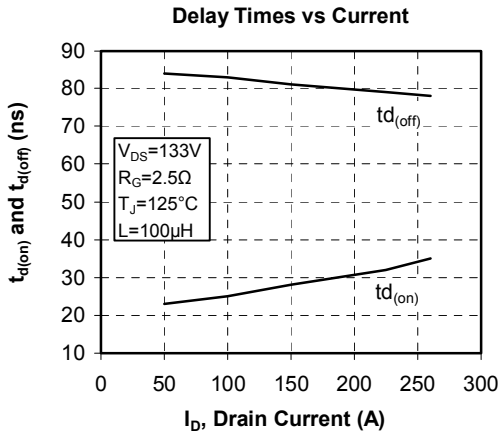
Package outline



Typical Performance Curve







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APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.